

INSULATED GATE BIPOLAR TRANSISTOR WITH ULTRAFAST SOFT RECOVERY DIODE

Features

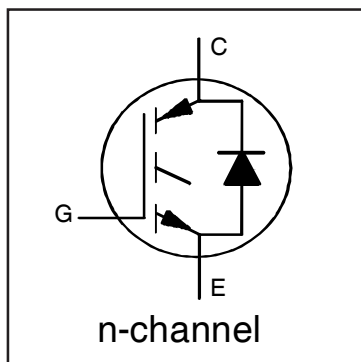
- Low $V_{CE(ON)}$ trench IGBT technology
- Low switching losses
- Square RBSOA
- 100% of the parts tested for I_{LM} ①
- Positive $V_{CE(ON)}$ temperature co-efficient
- Ultra fast soft recovery co-pak diode
- Tight parameter distribution
- Lead-Free

Benefits

- High efficiency in a wide range of applications
- Suitable for a wide range of switching frequencies due to low $V_{CE(ON)}$ and low switching losses
- Rugged transient performance for increased reliability
- Excellent current sharing in parallel operation

Applications

- U.P.S.
- Welding
- Solar Inverter
- Induction Heating

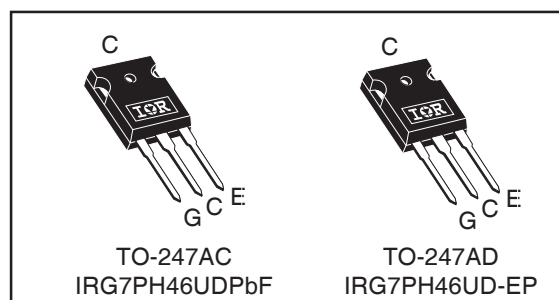


$$V_{CES} = 1200V$$

$$I_{NOMINAL} = 40A$$

$$T_{J(max)} = 150^{\circ}C$$

$$V_{CE(on)} \text{ typ.} = 1.7V$$



G	C	E
Gate	Collector	Emitter

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	1200	V
$I_C @ T_C = 25^{\circ}C$	Continuous Collector Current (Silicon Limited)	108	A
$I_C @ T_C = 100^{\circ}C$	Continuous Collector Current (Silicon Limited)	57	
$I_{NOMINAL}$	Nominal Current	40	
I_{CM}	Pulse Collector Current, $V_{GE} = 20V$	160	
I_{LM}	Clamped Inductive Load Current, $V_{GE} = 20V$ ①	160	
$I_F @ T_C = 25^{\circ}C$	Diode Continuous Forward Current	108	
$I_F @ T_C = 100^{\circ}C$	Diode Continuous Forward Current	57	
I_{FM}	Diode Maximum Forward Current ②	160	V
V_{GE}	Continuous Gate-to-Emitter Voltage	± 30	
$P_D @ T_C = 25^{\circ}C$	Maximum Power Dissipation	390	W
$P_D @ T_C = 100^{\circ}C$	Maximum Power Dissipation	156	
T_J	Operating Junction and	-55 to +150	$^{\circ}C$
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	
	Mounting Torque, 6-32 or M3 Screw	10 lbf-in (1.1 N·m)	

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$ (IGBT)	Thermal Resistance Junction-to-Case-(each IGBT) ④	—	—	0.32	$^{\circ}C/W$
$R_{\theta JC}$ (Diode)	Thermal Resistance Junction-to-Case-(each Diode) ④	—	—	0.66	
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink (flat, greased surface)	—	0.24	—	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (typical socket mount)	—	40	—	

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	1200	—	—	V	$V_{GE} = 0V, I_C = 100\mu A$ ③
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	1.2	—	V/ $^\circ\text{C}$	$V_{GE} = 0V, I_C = 1.0mA$ (25 $^\circ\text{C}$ -150 $^\circ\text{C}$)
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	—	1.7	2.0	V	$I_C = 40A, V_{GE} = 15V, T_J = 25^\circ\text{C}$
		—	2.0	—		$I_C = 40A, V_{GE} = 15V, T_J = 150^\circ\text{C}$
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	6.0	V	$V_{CE} = V_{GE}, I_C = 1.6mA$
$\Delta V_{GE(th)}/\Delta T_J$	Threshold Voltage temp. coefficient	—	-13	—	mV/ $^\circ\text{C}$	$V_{CE} = V_{GE}, I_C = 1.6mA$ (25 $^\circ\text{C}$ - 150 $^\circ\text{C}$)
g_{fe}	Forward Transconductance	—	50	—	S	$V_{CE} = 50V, I_C = 40A, PW = 20\mu s$
I_{CES}	Collector-to-Emitter Leakage Current	—	1.5	100	μA	$V_{GE} = 0V, V_{CE} = 1200V$
		—	2.0	—	mA	$V_{GE} = 0V, V_{CE} = 1200V, T_J = 150^\circ\text{C}$
V_{FM}	Diode Forward Voltage Drop	—	3.1	4.8	V	$I_F = 40A$
		—	3.0	—		$I_F = 40A, T_J = 150^\circ\text{C}$
I_{GES}	Gate-to-Emitter Leakage Current	—	—	± 200	nA	$V_{GE} = \pm 30V$

Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge (turn-on)	—	220	320	nC	$I_C = 40A$ ②
Q_{ge}	Gate-to-Emitter Charge (turn-on)	—	30	50		$V_{GE} = 15V$
Q_{gc}	Gate-to-Collector Charge (turn-on)	—	85	130		$V_{CC} = 600V$
E_{on}	Turn-On Switching Loss	—	2610	3515	μJ	$I_C = 40A, V_{CC} = 600V, V_{GE} = 15V$ ⑤
E_{off}	Turn-Off Switching Loss	—	1845	2725		$R_G = 10\Omega, L = 200\mu H, T_J = 25^\circ\text{C}$
E_{total}	Total Switching Loss	—	4455	6240		Energy losses include tail & diode reverse recovery
$t_{d(on)}$	Turn-On delay time	—	45	60	ns	
t_r	Rise time	—	40	60		
$t_{d(off)}$	Turn-Off delay time	—	410	450		
t_f	Fall time	—	45	60		
E_{on}	Turn-On Switching Loss	—	3790	—	μJ	$I_C = 40A, V_{CC} = 600V, V_{GE} = 15V$ ⑤
E_{off}	Turn-Off Switching Loss	—	2905	—		$R_G = 10\Omega, L = 200\mu H, T_J = 150^\circ\text{C}$
E_{total}	Total Switching Loss	—	6695	—		Energy losses include tail & diode reverse recovery
$t_{d(on)}$	Turn-On delay time	—	40	—	ns	
t_r	Rise time	—	40	—		
$t_{d(off)}$	Turn-Off delay time	—	480	—		
t_f	Fall time	—	200	—		
C_{ies}	Input Capacitance	—	4820	—	pF	$V_{GE} = 0V$
C_{oes}	Output Capacitance	—	150	—		$V_{CC} = 30V$
C_{res}	Reverse Transfer Capacitance	—	110	—		$f = 1.0MHz$
RBSOA	Reverse Bias Safe Operating Area	FULL SQUARE				$T_J = 150^\circ\text{C}, I_C = 160A$ $V_{CC} = 960V, V_p \leq 1200V$ $R_G = 10\Omega, V_{GE} = +20V$ to 0V
E_{rec}	Reverse Recovery Energy of the Diode	—	1130	—	μJ	$T_J = 150^\circ\text{C}$
t_{rr}	Diode Reverse Recovery Time	—	140	—	ns	$V_{CC} = 600V, I_F = 40A$
I_{rr}	Peak Reverse Recovery Current	—	40	—	A	$R_G = 10\Omega, L = 1.0mH$

Notes:

- ① $V_{CC} = 80\% (V_{CES}), V_{GE} = 20V, L = 200\mu H, R_G = 10\Omega$.
- ② Pulse width limited by max. junction temperature.
- ③ Refer to AN-1086 for guidelines for measuring $V_{(BR)CES}$ safely.
- ④ R_θ is measured at T_J of approximately 90 $^\circ\text{C}$.
- ⑤ Values influenced by parasitic L and C of the test circuit.

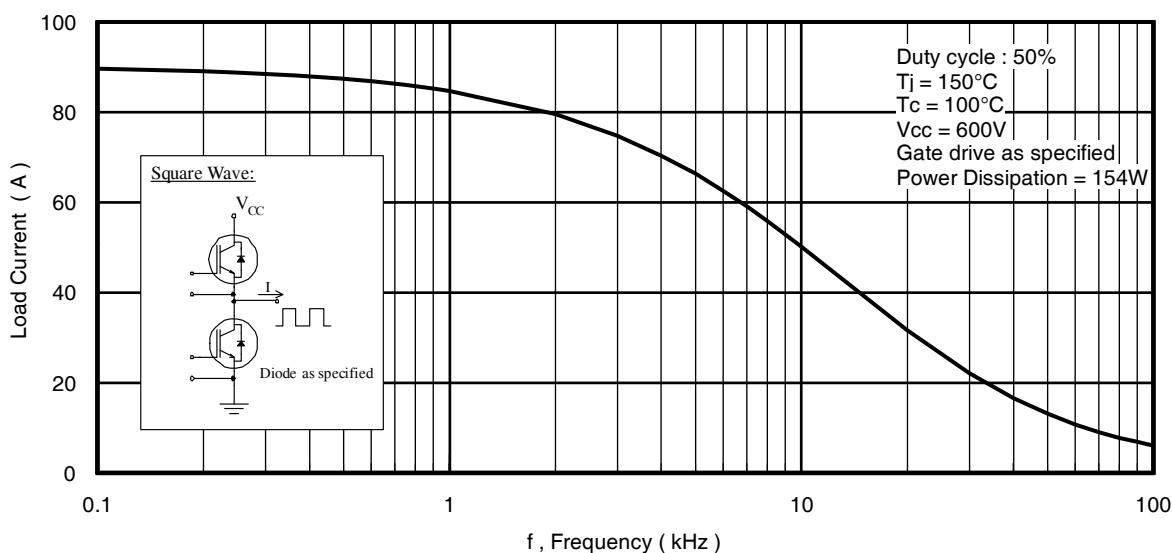


Fig. 1 - Typical Load Current vs. Frequency
 (Load Current = I_{RMS} of fundamental)

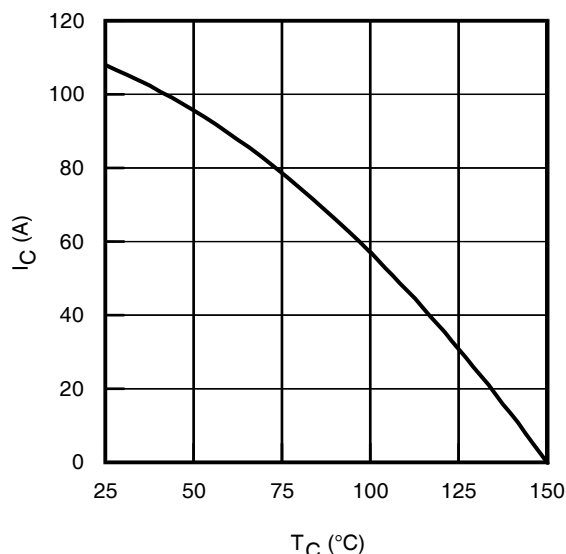


Fig. 1 - Maximum DC Collector Current vs. Case Temperature

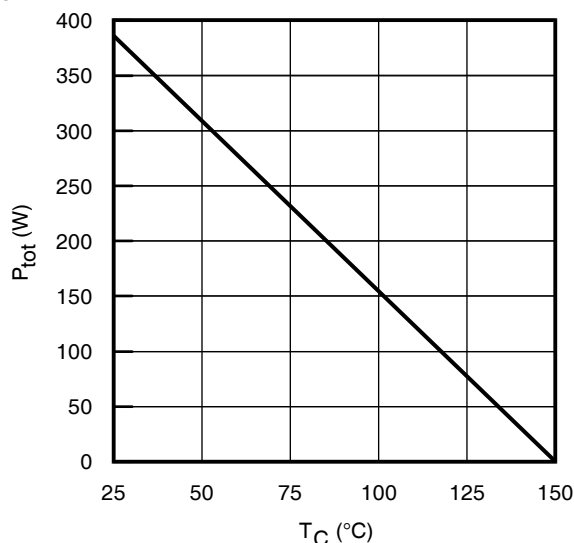


Fig. 2 - Power Dissipation vs. Case Temperature

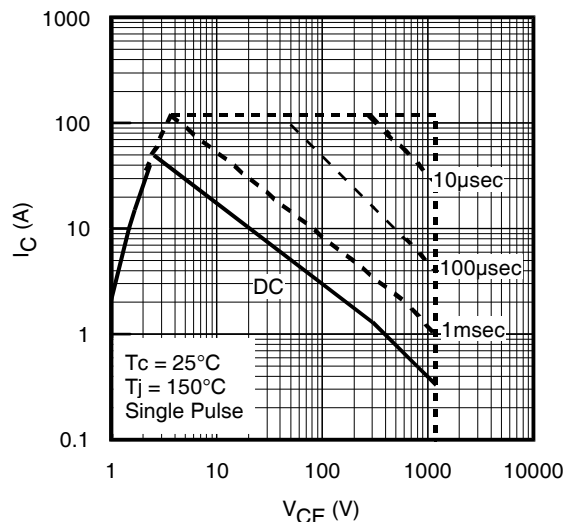


Fig. 3 - Forward SOA
 $T_C = 25^{\circ}\text{C}$, $T_J \leq 150^{\circ}\text{C}$; $V_{GE} = 15\text{V}$

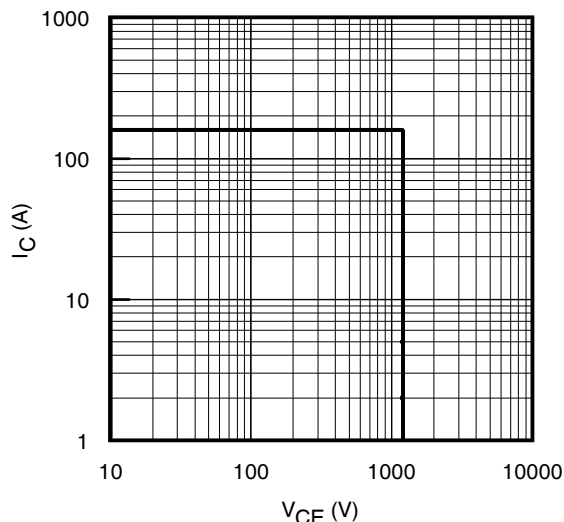


Fig. 4 - Reverse Bias SOA
 $T_J = 150^{\circ}\text{C}$; $V_{GE} = 20\text{V}$

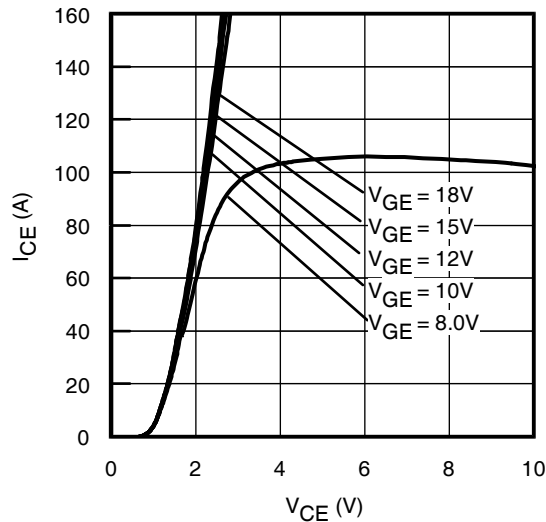


Fig. 5 - Typ. IGBT Output Characteristics
 $T_J = -40^{\circ}\text{C}$; $t_p = 30\mu\text{s}$

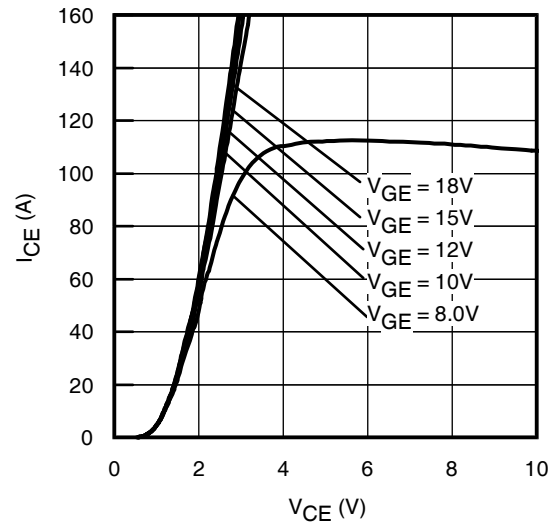


Fig. 6 - Typ. IGBT Output Characteristics
 $T_J = 25^{\circ}\text{C}$; $t_p = 30\mu\text{s}$

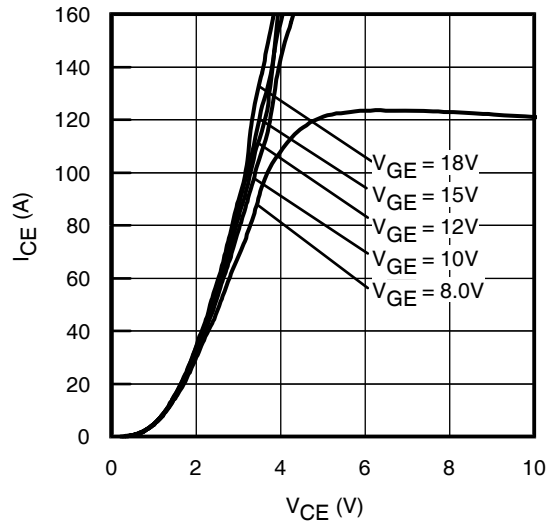


Fig. 7 - Typ. IGBT Output Characteristics
 $T_J = 150^{\circ}\text{C}$; $t_p = 30\mu\text{s}$

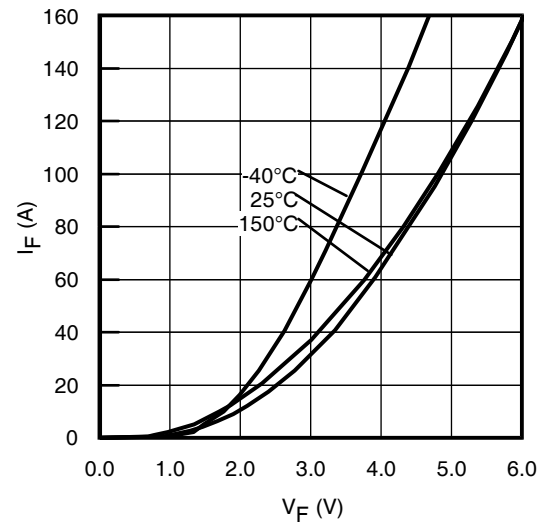


Fig. 8 - Typ. Diode Forward Characteristics
 $t_p = 30\mu\text{s}$

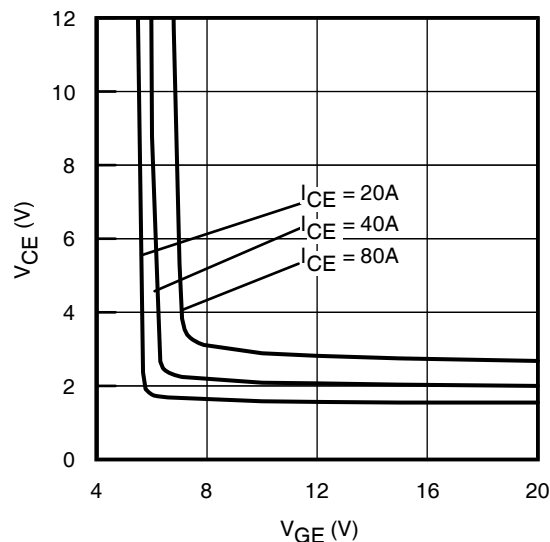


Fig. 9 - Typical V_{CE} vs. V_{GE}
 $T_J = -40^{\circ}\text{C}$

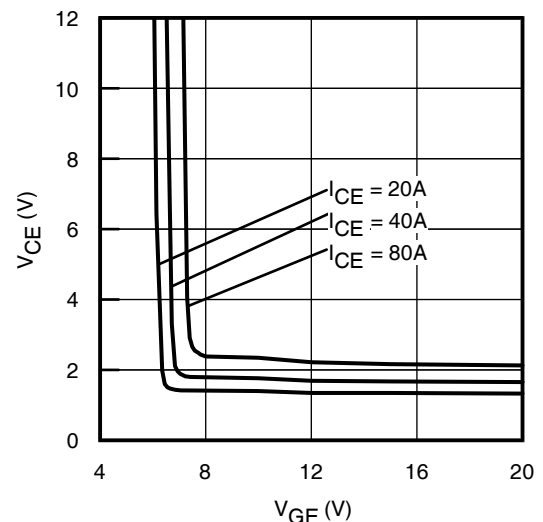


Fig. 10 - Typical V_{CE} vs. V_{GE}
 $T_J = 25^{\circ}\text{C}$

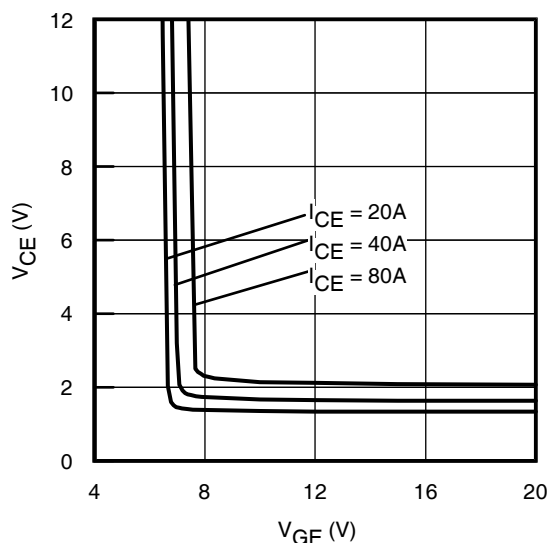


Fig. 11 - Typical V_{CE} vs. V_{GE}
 $T_J = 150^\circ\text{C}$

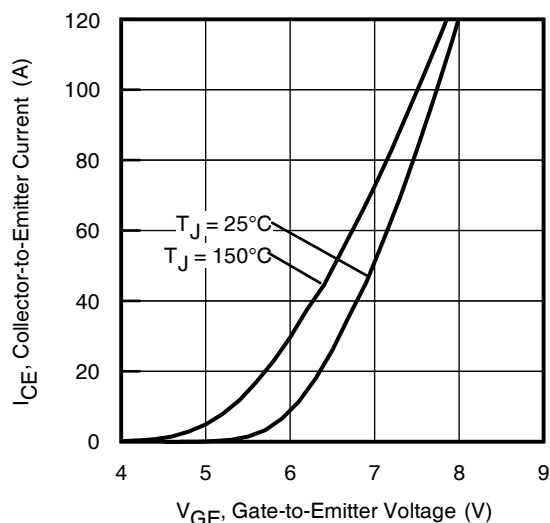


Fig. 12 - Typ. Transfer Characteristics
 $V_{CE} = 50\text{V}$

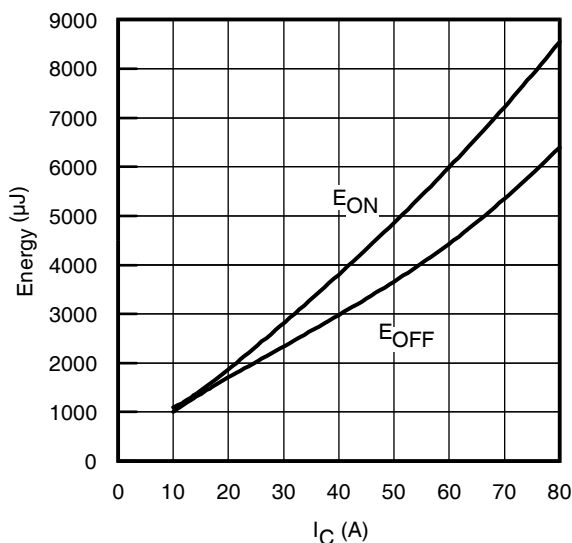


Fig. 13 - Typ. Energy Loss vs. I_C
 $T_J = 150^\circ\text{C}$; $L = 200\mu\text{H}$; $V_{CE} = 600\text{V}$; $R_G = 10\Omega$; $V_{GE} = 15\text{V}$

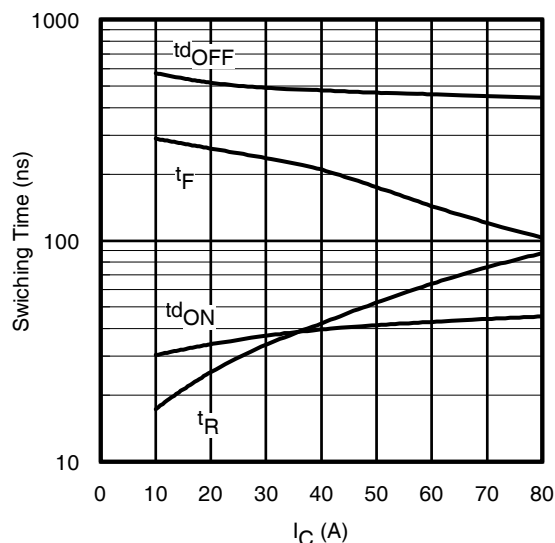


Fig. 14 - Typ. Switching Time vs. I_C
 $T_J = 150^\circ\text{C}$; $L = 200\mu\text{H}$; $V_{CE} = 600\text{V}$; $R_G = 10\Omega$; $V_{GE} = 15\text{V}$

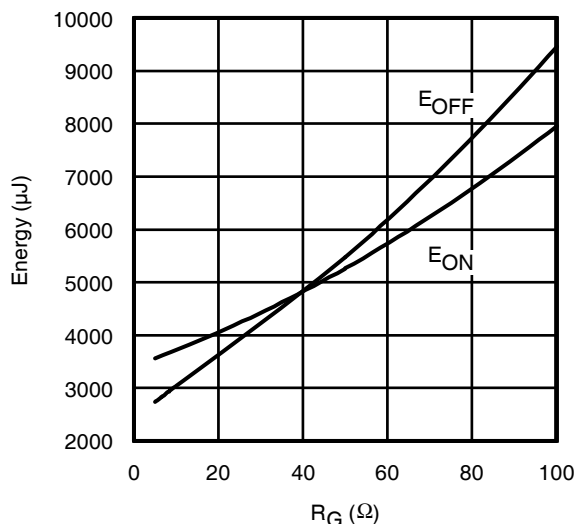


Fig. 15 - Typ. Energy Loss vs. R_G
 $T_J = 150^\circ\text{C}$; $L = 200\mu\text{H}$; $V_{CE} = 600\text{V}$; $I_{CE} = 40\text{A}$; $V_{GE} = 15\text{V}$

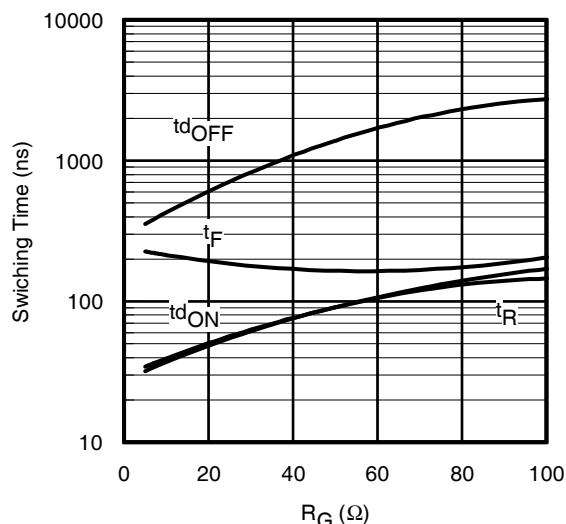


Fig. 16 - Typ. Switching Time vs. R_G
 $T_J = 150^\circ\text{C}$; $L = 200\mu\text{H}$; $V_{CE} = 600\text{V}$; $I_{CE} = 40\text{A}$; $V_{GE} = 15\text{V}$

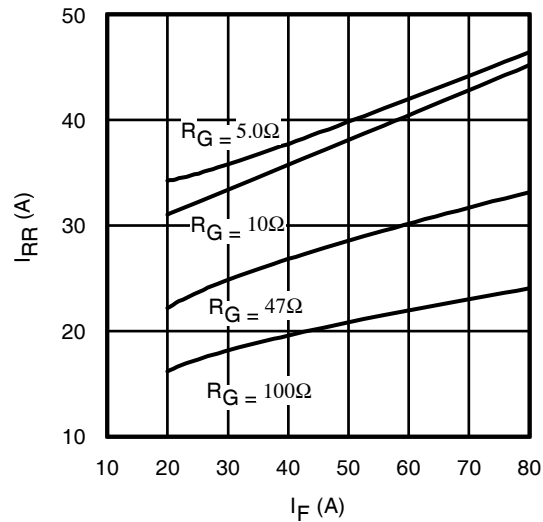


Fig. 17 - Typ. Diode I_{RR} vs. I_F
 $T_J = 150^\circ\text{C}$

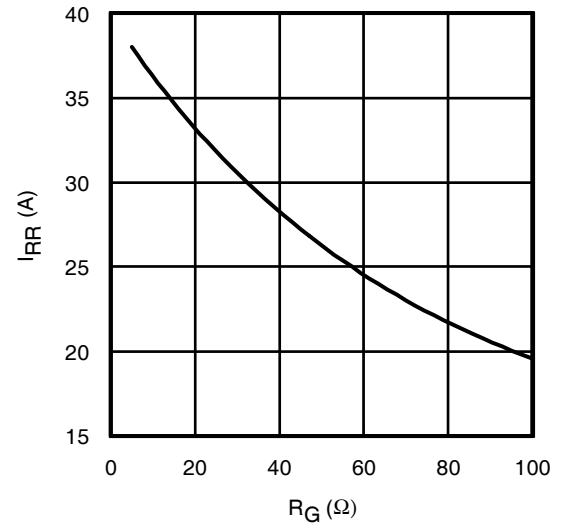


Fig. 18 - Typ. Diode I_{RR} vs. R_G
 $T_J = 150^\circ\text{C}$

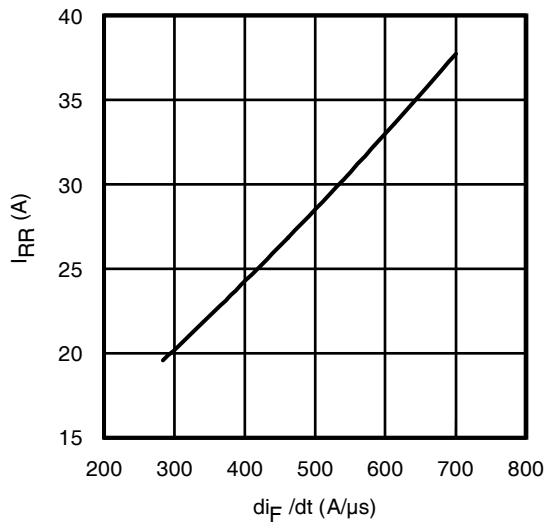


Fig. 19 - Typ. Diode I_{RR} vs. di_F/dt
 $V_{CC} = 600\text{V}$; $V_{GE} = 15\text{V}$; $I_F = 40\text{A}$; $T_J = 150^\circ\text{C}$

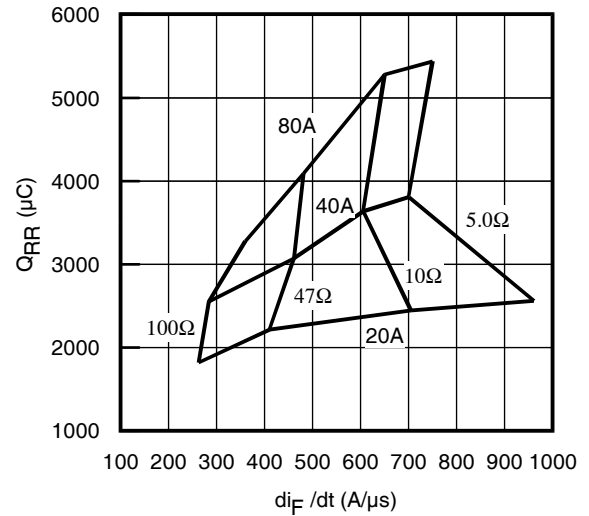


Fig. 20 - Typ. Diode Q_{RR} vs. di_F/dt
 $V_{CC} = 600\text{V}$; $V_{GE} = 15\text{V}$; $T_J = 150^\circ\text{C}$

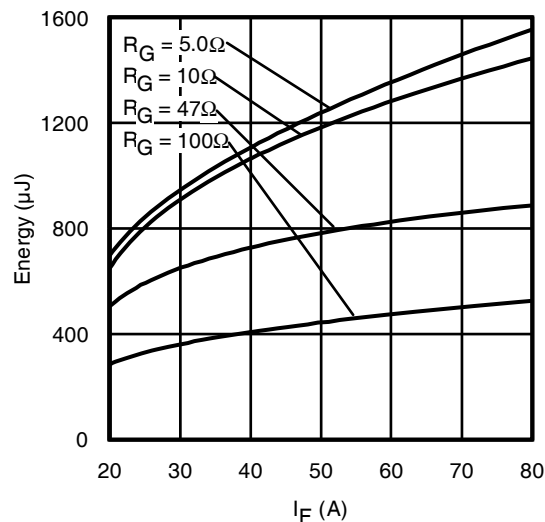


Fig. 21 - Typ. Diode E_{RR} vs. I_F
 $T_J = 150^\circ\text{C}$

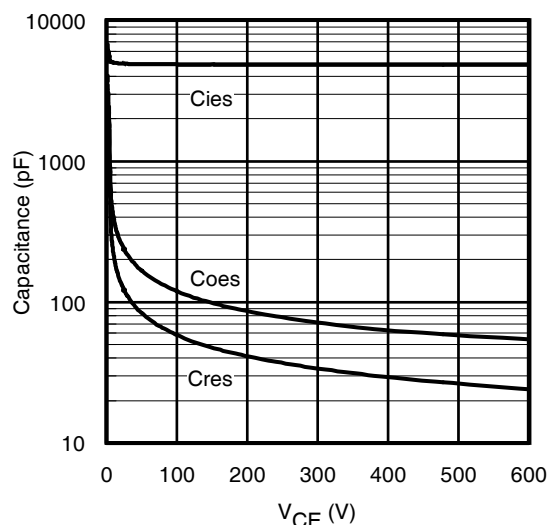


Fig. 22 - Typ. Capacitance vs. V_{CE}
 $V_{GE} = 0V$; $f = 1MHz$

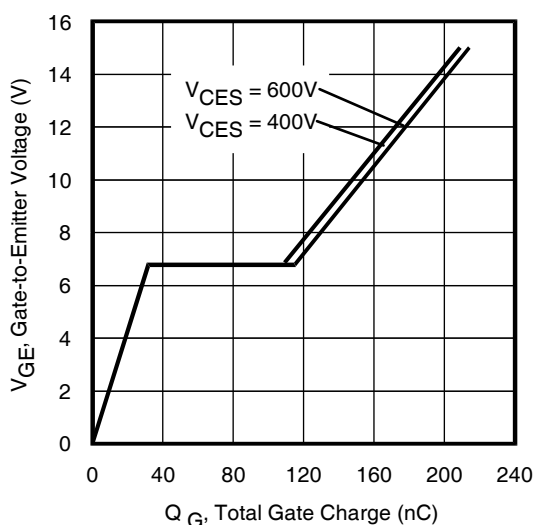


Fig. 23 - Typical Gate Charge vs. V_{GE}
 $I_{CE} = 40A$; $L = 2400H$

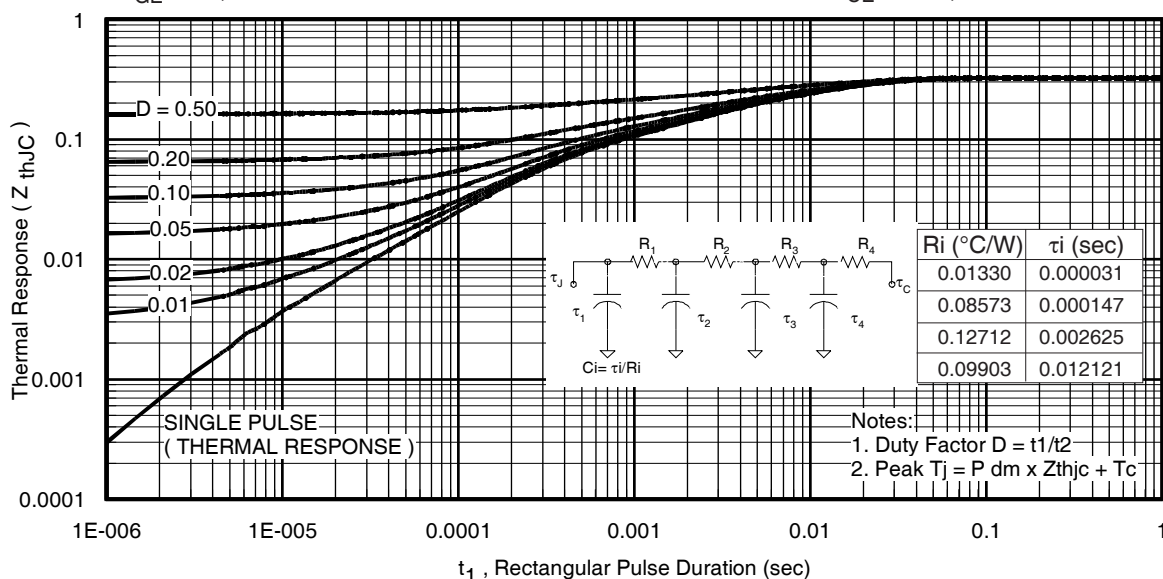


Fig. 24. Maximum Transient Thermal Impedance, Junction-to-Case (IGBT)

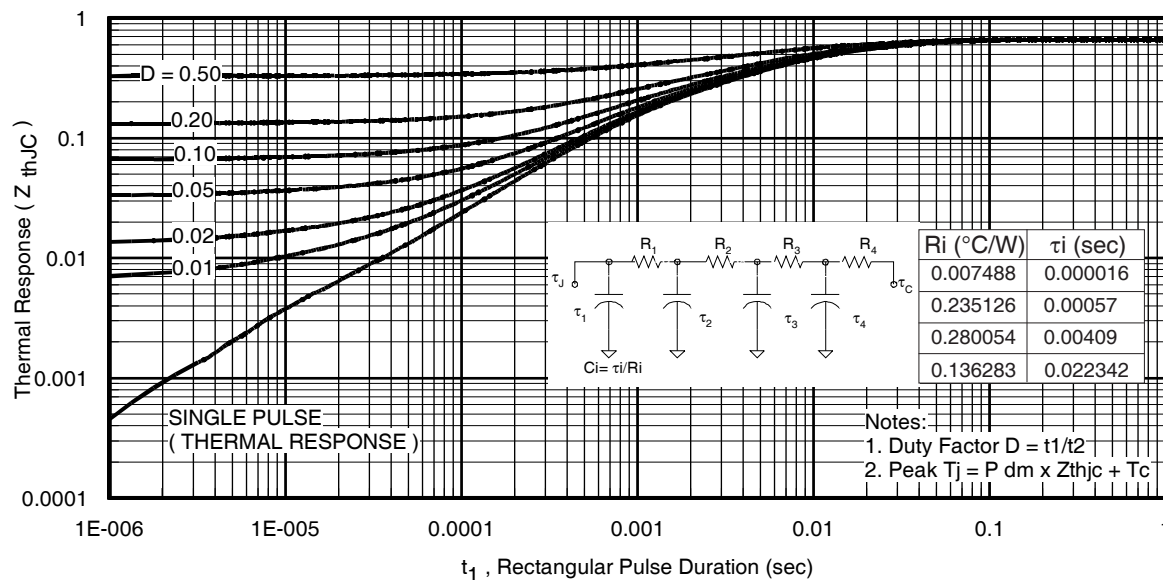
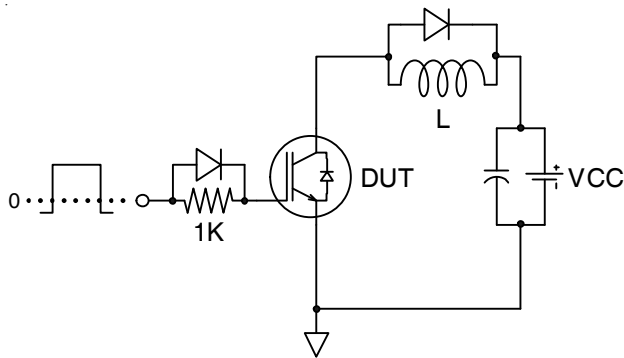
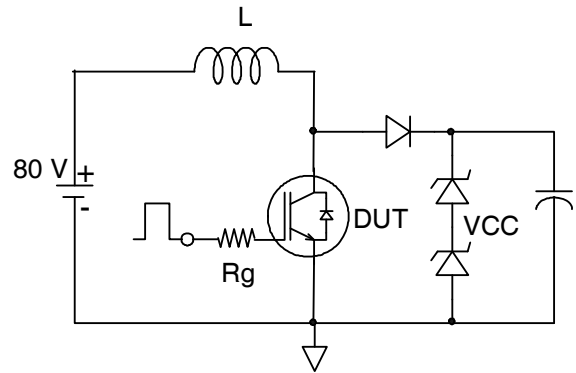
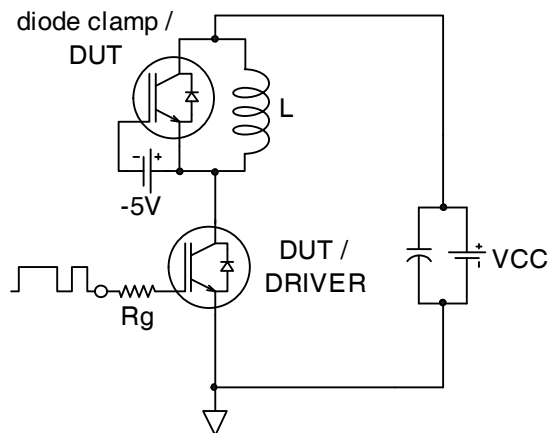
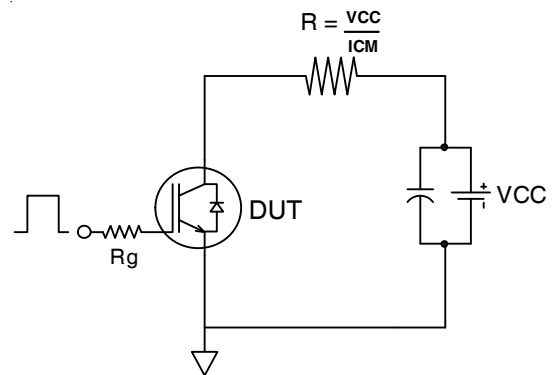
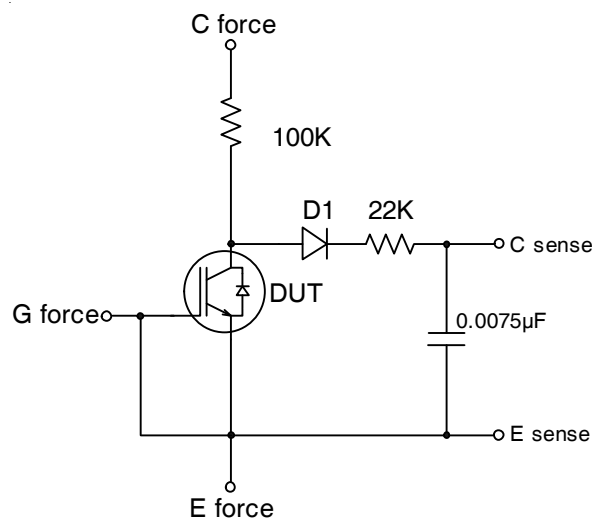


Fig. 25. Maximum Transient Thermal Impedance, Junction-to-Case (DIODE)


Fig.C.T.1 - Gate Charge Circuit (turn-off)

Fig.C.T.2 - RBSOA Circuit

Fig.C.T.3 - Switching Loss Circuit

Fig.C.T.4 - Resistive Load Circuit

Fig.C.T.5 - BVCEs Filter Circuit

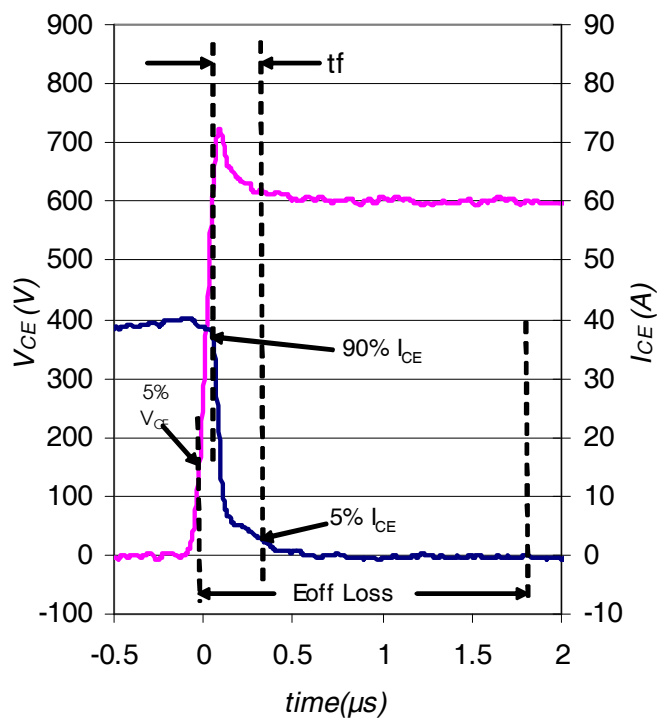


Fig. WF1 - Typ. Turn-off Loss Waveform
@ $T_J = 150^\circ\text{C}$ using Fig. CT.4

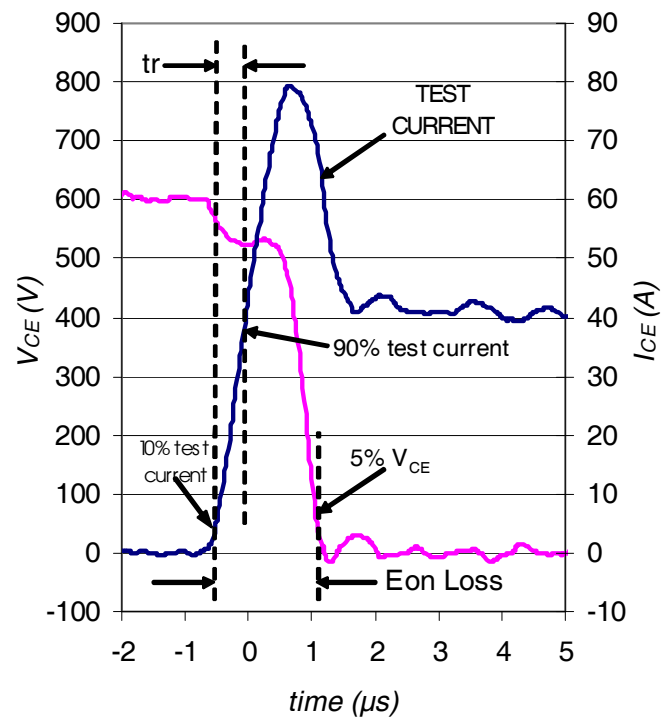


Fig. WF2 - Typ. Turn-on Loss Waveform
@ $T_J = 150^\circ\text{C}$ using Fig. CT.4

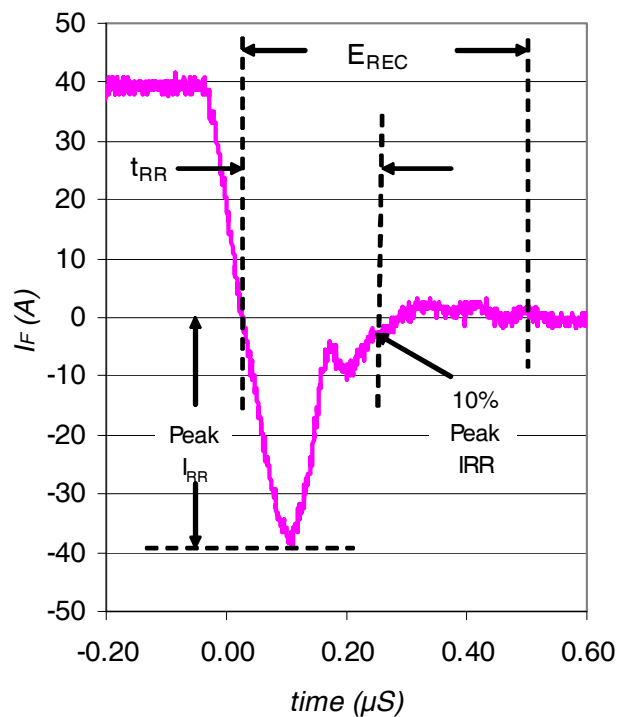
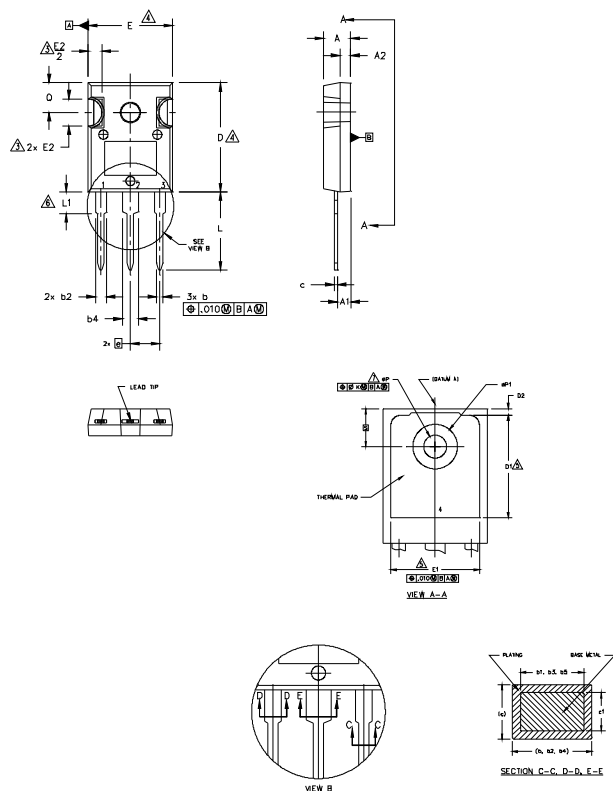


Fig. WF3 - Typ. Diode Recovery Waveform
@ $T_J = 150^\circ\text{C}$ using Fig. CT.4

TO-247AC Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

1. DIMENSIONING AND TOLERANCING AS PER ASME Y14.5M 1994.
2. DIMENSIONS ARE SHOWN IN INCHES.
3. CONTOUR OF SLOT OPTIONAL.
4. DIMENSION D & E DO NOT INCLUDE MOLD FLASH; MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
5. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS D1 & E1.
6. LEAD FINISH UNCONTROLLED IN L1.
7. ØP TO HAVE A MAXIMUM DRAFT ANGLE OF 1.5 ° TO THE TOP OF THE PART WITH A MAXIMUM HOLE DIAMETER OF .154 INCH.
8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-247AC .

SYMBOL	DIMENSIONS				NOTES
	INCHES		MILLIMETERS		
	MIN.	MAX.	MIN.	MAX.	
A	.183	.209	4.65	5.31	
A1	.087	.102	2.21	2.59	
A2	.059	.098	1.50	2.49	
b	.039	.055	0.99	1.40	
b1	.039	.053	0.99	1.35	
b2	.065	.094	1.65	2.39	
b3	.065	.092	1.65	2.34	
b4	.102	.135	2.59	3.43	
b5	.102	.133	2.59	3.38	
c	.015	.035	0.38	0.89	
c1	.015	.033	0.38	0.84	4
D	.776	.815	19.71	20.70	
D1	.515	—	13.08	—	
D2	.020	.053	0.51	1.35	
E	.602	.625	15.29	15.87	
E1	.530	—	13.46	—	4
E2	.178	.216	4.52	5.49	
e	.215 BSC		5.46 BSC		
ek	.010		0.25		
L	.559	.634	14.20	16.10	
L1	.146	.169	3.71	4.29	
ØP	.140	.144	3.56	3.66	
ØP1	—	.291	—	7.39	
Q	.209	.224	5.31	5.69	
S	.217 BSC		5.51 BSC		

LEAD ASSIGNMENTS

HEXFET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

IGBTs, CoPACK

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER
- 4.- COLLECTOR

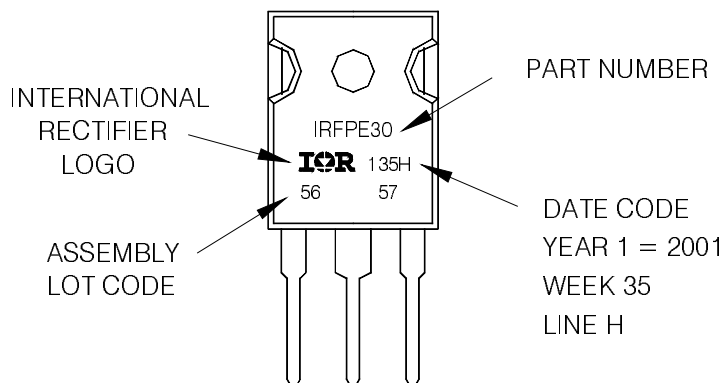
DIODES

- 1.- ANODE/OPEN
- 2.- CATHODE
- 3.- ANODE

TO-247AC Part Marking Information

EXAMPLE: THIS IS AN IRFPE30
WITH ASSEMBLY
LOT CODE 5657
ASSEMBLED ON WW 35, 2001
IN THE ASSEMBLY LINE "H"

Note: "P" in assembly line position
indicates "Lead-Free"

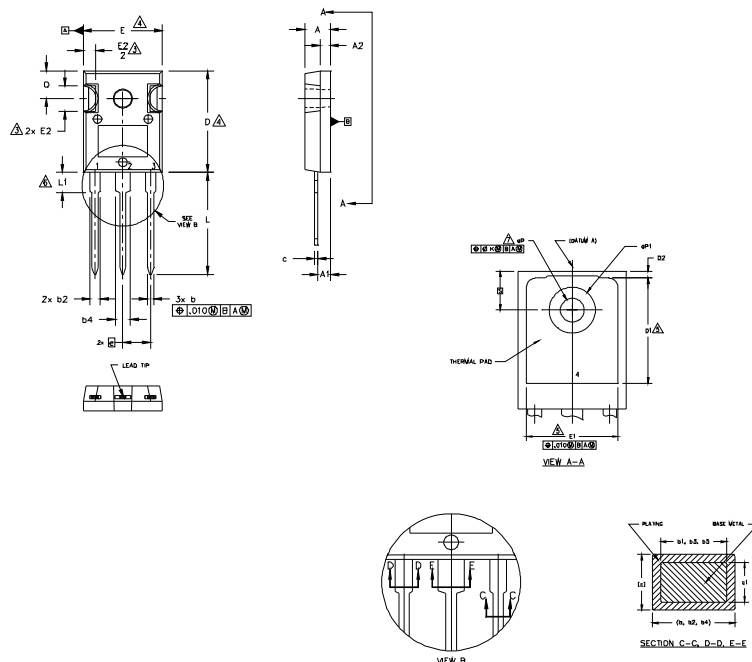


TO-247AC package is not recommended for Surface Mount Application.

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

TO-247AD Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

1. DIMENSIONING AND TOLERANCING AS PER ASME Y14.5M 1994.
2. DIMENSIONS ARE SHOWN IN INCHES.
3. CONTOUR OF SLOT OPTIONAL.
4. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
5. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS D1 & E1.
6. LEAD FINISH UNCONTROLLED IN L1.
7. ØP TO HAVE A MAXIMUM DRAFT ANGLE OF 1.5 ° TO THE TOP OF THE PART WITH A MAXIMUM HOLE DIAMETER OF .154 INCH.
8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-247AD.

SYMBOL	DIMENSIONS				NOTE
	INCHES		MILLIMETERS		
	MIN.	MAX.	MIN.	MAX.	
A	.183	.209	4.65	5.31	
A1	.087	.102	2.21	2.59	
A2	.059	.098	1.50	2.49	
b	.039	.055	0.99	1.40	
b1	.039	.053	0.99	1.35	
b2	.065	.094	1.65	2.39	
b3	.065	.092	1.65	2.34	
b4	.102	1.35	2.59	3.43	
b5	.102	1.33	2.59	3.38	
c	.015	.035	0.38	0.89	
c1	.015	.033	0.38	0.84	
D	.776	.816	19.71	20.70	4
D1	.515	—	13.08	—	5
D2	.020	.053	0.51	1.35	
E	.602	.625	15.29	15.87	
E1	.530	—	13.46	—	
E2	.178	.216	4.52	5.49	
e	.215 BSC		.546 BSC		
gk	.010		0.25		
L	.780	.827	19.57	21.00	
L1	.146	.169	3.71	4.29	
p	.140	.144	3.56	3.66	
øP1	—	.291	—	7.39	
Q	.209	.224	5.31	5.69	
S	.217 BSC		.551 BSC		

LEAD ASSIGNMENTS

- HEXFET
- 1.- GATE
 - 2.- DRAIN
 - 3.- SOURCE
 - 4.- DRAIN

IGBTs, CoPACK

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER
- 4.- COLLECTOR

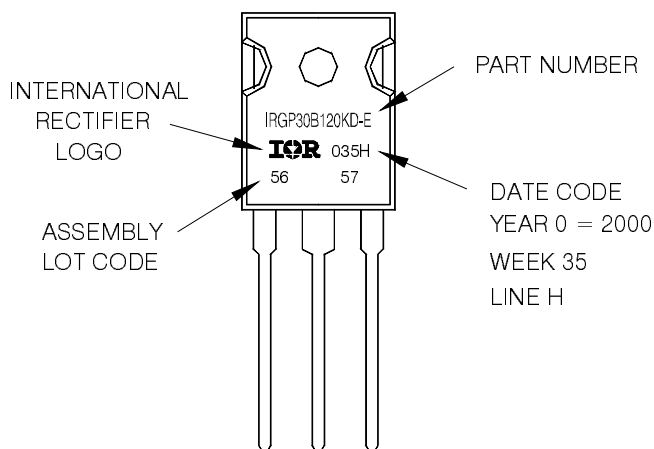
DIODES

- 1.- ANODE/OPEN
- 2.- CATHODE
- 3.- ANODE

TO-247AD Part Marking Information

EXAMPLE: THIS IS AN IRGP30B120KD-E
WITH ASSEMBLY
LOT CODE 5657
ASSEMBLED ON WW 35, 2000
IN THE ASSEMBLY LINE "H"

Note: "P" in assembly line position indicates "Lead-Free"



TO-247AD package is not recommended for Surface Mount Application.

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

Компания «Океан Электроники» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Поставка оригинальных импортных электронных компонентов напрямую с производств Америки, Европы и Азии, а так же с крупнейших складов мира;
- Широкая линейка поставок активных и пассивных импортных электронных компонентов (более 30 млн. наименований);
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Помощь Конструкторского Отдела и консультации квалифицированных инженеров;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Поставка электронных компонентов под контролем ВП;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- При необходимости вся продукция военного и аэрокосмического назначения проходит испытания и сертификацию в лаборатории (по согласованию с заказчиком);
- Поставка специализированных компонентов военного и аэрокосмического уровня качества (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Actel, Aeroflex, Peregrine, VPT, Syfer, Eurofarad, Texas Instruments, MS Kennedy, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Компания «Океан Электроники» является официальным дистрибьютором и эксклюзивным представителем в России одного из крупнейших производителей разъемов военного и аэрокосмического назначения «JONHON», а так же официальным дистрибьютором и эксклюзивным представителем в России производителя высокотехнологичных и надежных решений для передачи СВЧ сигналов «FORSTAR».



JONHON

«JONHON» (основан в 1970 г.)

Разъемы специального, военного и аэрокосмического назначения:

(Применяются в военной, авиационной, аэрокосмической, морской, железнодорожной, горно- и нефтедобывающей отраслях промышленности)

«FORSTAR» (основан в 1998 г.)

ВЧ соединители, коаксиальные кабели,
кабельные сборки и микроволновые компоненты:

(Применяются в телекоммуникациях гражданского и специального назначения, в средствах связи, РЛС, а так же военной, авиационной и аэрокосмической отраслях промышленности).



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